

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	("RIE" near4 photoresist) same remov\$4 and (low near8 angle)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 08:20
L2	7	((("RIE" or "reactive ion etching") near4 photoresist) same remov\$4 and (low near8 angle)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 08:21
L4	16	(ion near etch\$4) same "low angle"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:56
L5	7	(ion near etch\$4) same "low angle" and RIE	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:01
L6	1	(ion near etch\$4) same "low angle" and RIE and (remain\$4 near photoresist)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:59
L7	1	(ion near etch\$4) same "low angle" and RIE and (remain\$4 near8 photoresist)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:00
L8	2	(ion near etch\$4) same "low angle" and RIE and photoresist and mask and remov\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:00
L9	1	(ion near etch\$4) same "low angle" and RIE and photoresist and mask and remov\$4 and dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:00

L10	6	(ion near etch\$4) same "low angle" and RIE and dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:05
L11	1	(ion near etch\$4) same "low angle" and RIE and dielectric and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:01
L12	2	(ion near etch\$4) same (low adj angle) and RIE and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:05